

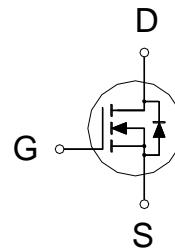
**NIKO-SEM****N-Channel Enhancement Mode  
Field Effect Transistor****PKCS0BB**

PDFN 5x6P

Halogen-Free &amp; Lead-Free

**PRODUCT SUMMARY**

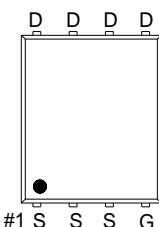
$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D^4$
40V	1.5mΩ	177A

**Features**

- Pb-Free, Halogen Free and RoHS compliant.
- Low  $R_{DS(on)}$  to Minimize Conduction Losses.
- Ohmic Region Good  $R_{DS(on)}$  Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

**Applications**

- Protection Circuits Applications.
- Computer for DC to DC Converters Applications.



G. GATE  
D. DRAIN  
S. SOURCE

#1 S S S G  
100% UIS Tested  
100% Rg Tested

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>4</sup>	$T_C = 25^\circ\text{C}$	$I_D$	177	A
	$T_C = 100^\circ\text{C}$		112	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	400	A
Continuous Drain Current	$T_A = 25^\circ\text{C}$	$I_D$	35	
	$T_A = 70^\circ\text{C}$		28	
Avalanche Current		$I_{AS}$	71	
Avalanche Energy	$L = 0.1\text{mH}$	$E_{AS}$	252	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	104	W
	$T_C = 100^\circ\text{C}$		41	
Power Dissipation <sup>3</sup>	$T_A = 25^\circ\text{C}$	$P_D$	4.1	W
	$T_A = 70^\circ\text{C}$		2.6	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	°C

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**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient <sup>2</sup>	$t \leq 10s$	$R_{\theta JA}$		30	°C / W
Junction-to-Ambient <sup>2</sup>	Steady-State	$R_{\theta JA}$		47	
Junction-to-Case	Steady-State	$R_{\theta JC}$		1.2	

<sup>1</sup>Pulse width limited by maximum junction temperature.<sup>2</sup>The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ C$ .<sup>3</sup>The Power dissipation is based on  $R_{\theta JA} t \leq 10s$  value.<sup>4</sup>The maximum current rating is package limited.**ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ C$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.8	2.3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 32V, V_{GS} = 0V$			1	$\mu A$
		$V_{DS} = 30V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 16A$		1.5	2.1	$m\Omega$
		$V_{GS} = 10V, I_D = 20A$		1.1	1.5	
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 5V, I_D = 20A$		84		S
<b>DYNAMIC</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 20V, f = 1MHz$		6072		pF
Output Capacitance	$C_{oss}$			694		
Reverse Transfer Capacitance	$C_{rss}$			377		
Gate Resistance	$R_g$	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.6		$\Omega$
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{GS} = 10V$ $V_{GS} = 4.5V$ $V_{DS} = 20V, V_{GS} = 10V, I_D = 20A$		109		nC
				55		
Gate-Source Charge <sup>2</sup>	$Q_{gs}$			18		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$			22		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$			31		
Rise Time <sup>2</sup>	$t_r$			79		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$	$V_{DS} = 20V, I_D \approx 20A, V_{GS} = 10V, R_{GEN} = 6\Omega$		167		nS
Fall Time <sup>2</sup>	$t_f$			119		

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**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ )**

Continuous Current	$I_S$				80	A
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = 20\text{A}, V_{GS} = 0\text{V}$			1.3	V
Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{A}, dI_F/dt = 100\text{A} / \mu\text{s}$	37			nS
Reverse Recovery Charge	$Q_{rr}$		28			nC

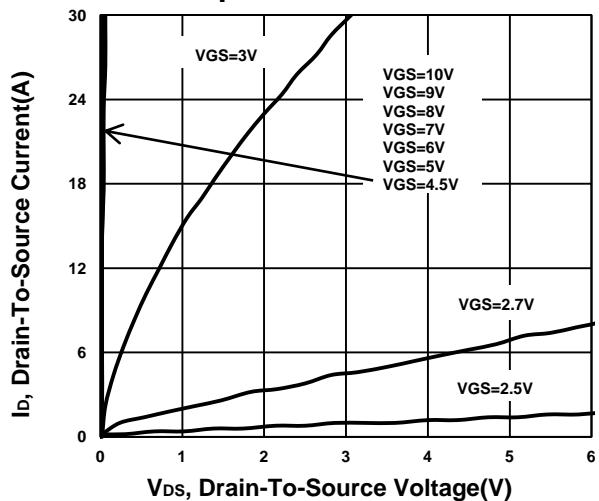
<sup>1</sup>Pulse test : Pulse Width  $\leq 300 \mu\text{sec}$ , Duty Cycle  $\leq 2\%$ .<sup>2</sup>Independent of operating temperature.

**NIKO-SEM**

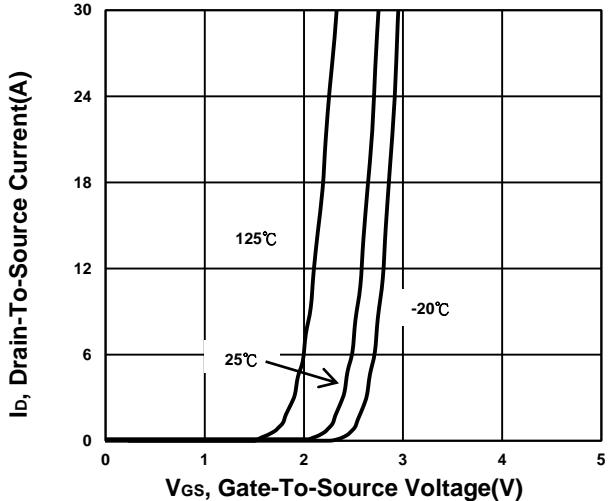
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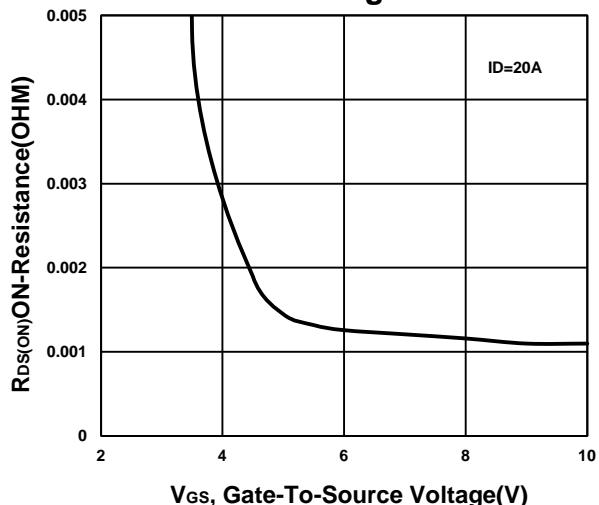
**Output Characteristics**



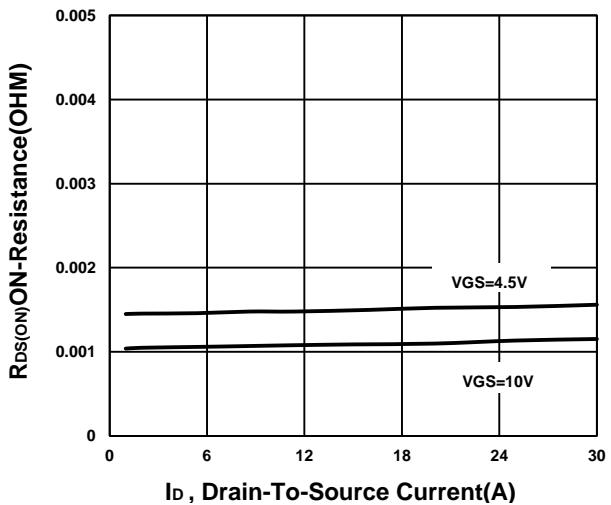
**Transfer Characteristics**



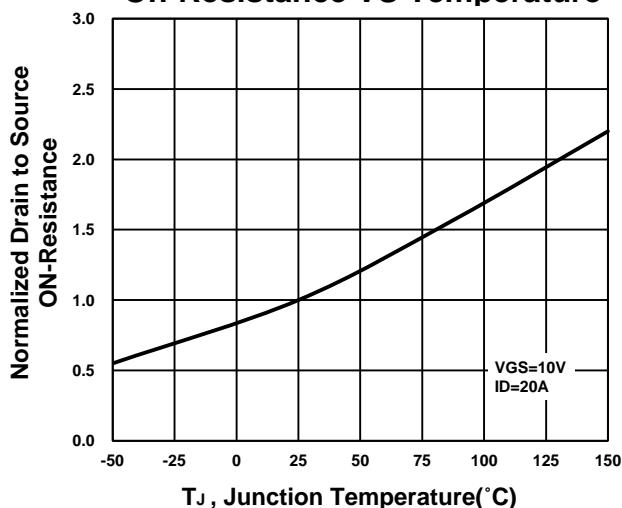
**On-Resistance VS Gate-To-Source Voltage**



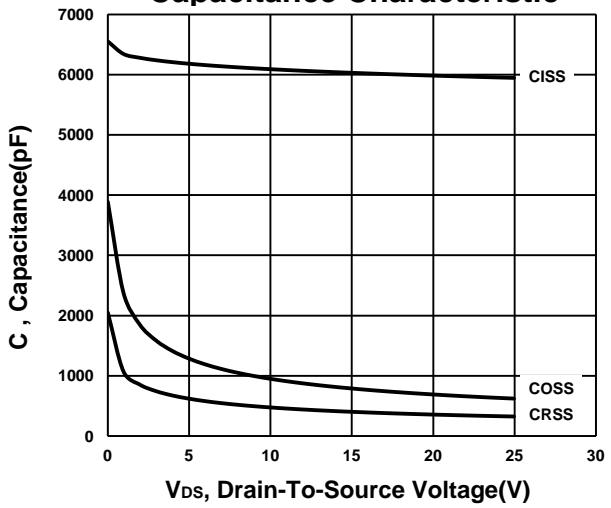
**On-Resistance VS Drain Current**

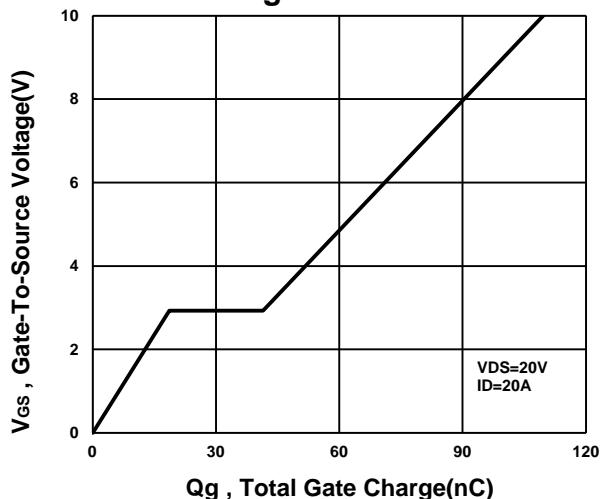
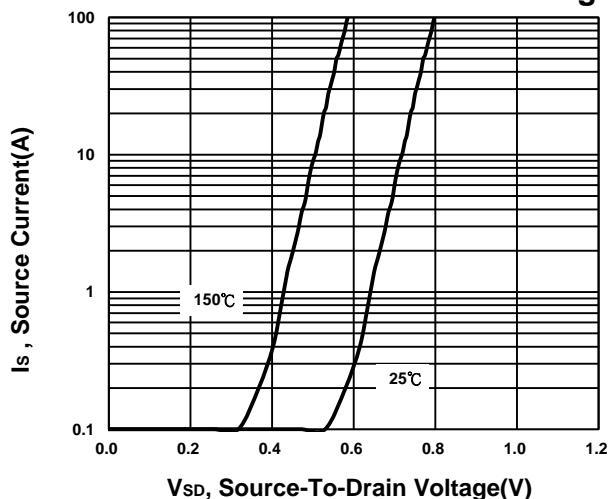
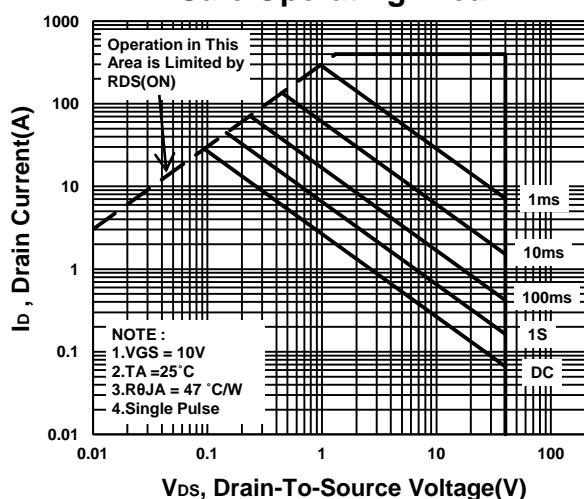
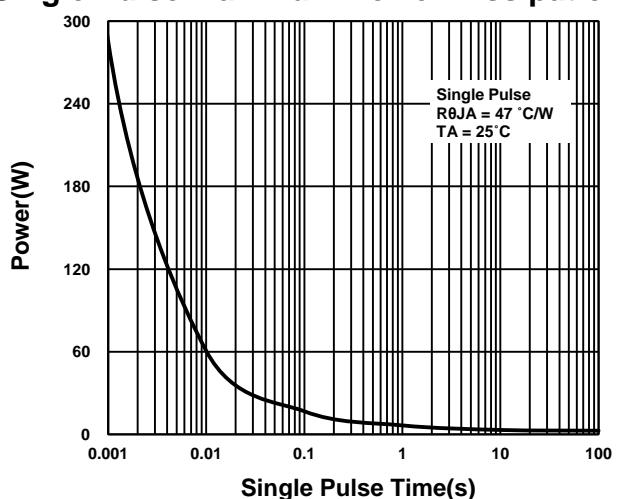
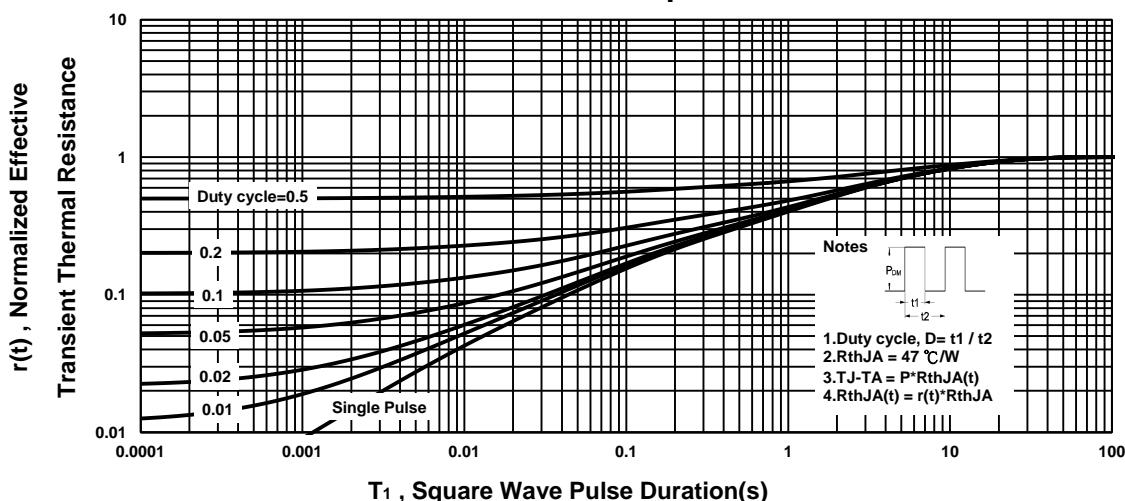


**On-Resistance VS Temperature**



**Capacitance Characteristic**



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Halogen-Free & Lead-Free****Gate charge Characteristics****Source-Drain Diode Forward Voltage****Safe Operating Area****Single Pulse Maximum Power Dissipation****Transient Thermal Response Curve**

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